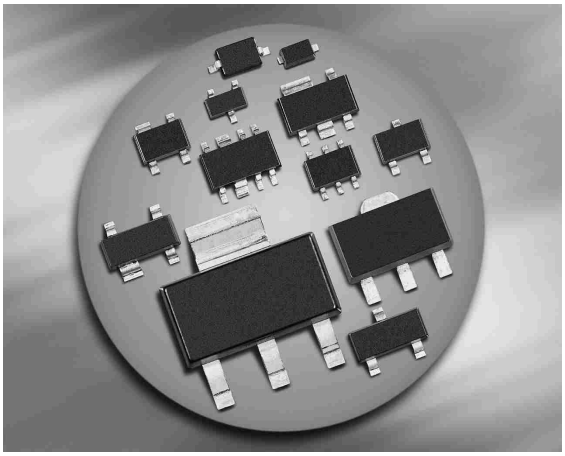
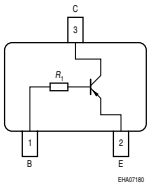
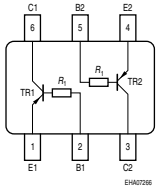
PNP Silicon Digital Transistor

- Switching circuit, inverter, interface circuit, driver circuit.
- Built in bias resistor (R_1 = 10kΩ)
- For 6-PIN packages: two (galvanic) internal isolated transistors with good matching in one package



BCR179F/L3 **SEMB4**
BCR179T





Type	Marking	Pin Configuration						Package
BCR179F	WWs	1=B	2=E	3=C	-	-	-	TSFP-3
BCR179L3	WW	1=B	2=E	3=C	-	-	-	TSLP-3-4
BCR179T	WWs	1=B	2=E	3=C	-	-	-	SC75
SEMB4	WW	1=E1	2=B1	3=C2	4=E2	5=B2	6=C1	SOT666

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	50	V
Collector-base voltage	V_{CBO}	50	
Emitter-base voltage	V_{EBO}	5	
Input on voltage	$V_{i(on)}$	20	
Collector current	I_C	100	mA
Total power dissipation	P_{tot}		mW
BCR179F, $T_S \leq 128°C$		250	
BCR179L3, $T_S \leq 135°C$		250	
BCR179T, $T_S \leq 109°C$		250	
SEMB4, $T_S \leq 75°C$		250	
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	150 ... -65	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[1)]	R_{thJS}		K/W
BCR179F		≤ 90	
BCR179L3		≤ 60	
BCR179T		≤ 109	
SEMB4		≤ 300	

[1]For calculation of R_{thJA} please refer to Application Note Thermal Resistance

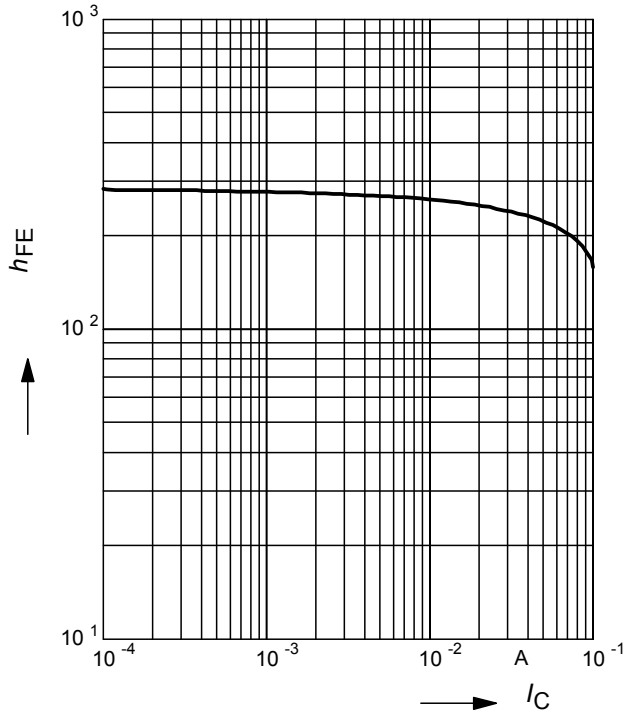
Electrical Characteristics at T_A = 25°C, unless otherwise specified

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 100 µA, I_B = 0	$V_{(BR)CEO}$	50	-	-	V
Collector-base breakdown voltage I_C = 10 µA, I_E = 0	$V_{(BR)CBO}$	50	-	-	
Emitter-base breakdown voltage I_E = 10 µA, I_C = 0	$V_{(BR)EBO}$	5	-	-	
Collector-base cutoff current V_{CB} = 40 V, I_E = 0	I_{CBO}	-	-	100	nA
DC current gain[1)] I_C = 5 mA, V_{CE} = 5 V	h_{FE}	120	-	630	-
Collector-emitter saturation voltage[1)] I_C = 10 mA, I_B = 0,5 mA	V_{CEsat}	-	-	0,3	V
Input off voltage I_C = 100 °C, V_{CE} = 5 V	$V_{i(off)}$	0,4	-	1	
Input on voltage I_C = 2 mA, V_{CE} = 0,3 V	$V_{i(on)}$	0,5	-	1,1	
Input resistor	R_1	7	10	13	kΩ
AC Characteristics					
Transition frequency I_C = 10 mA, V_{CE} = 5 V, f = 100 MHz	f_T	-	150	-	MHz
Collector-base capacitance V_{CB} = 10 V, f = 1 MHz	C_{cb}	-	1,2	-	pF

[1]Pulse test: t < 300µs; D < 2%

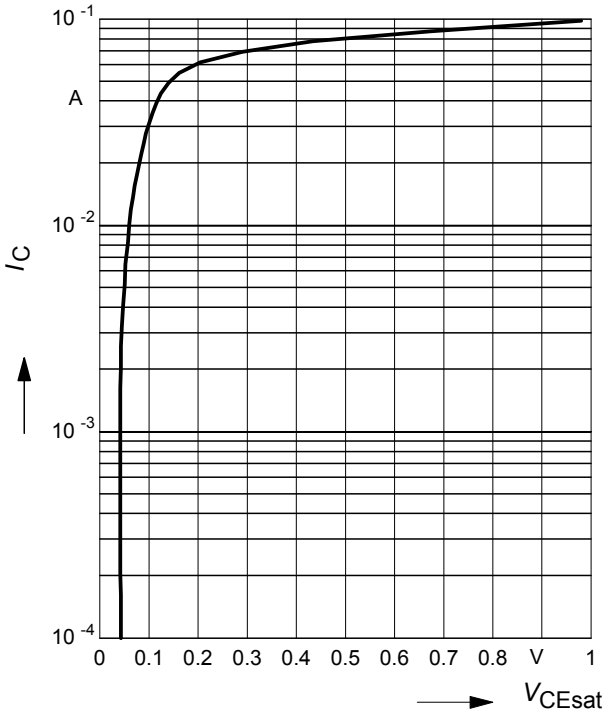
DC current gain $h_{FE} = f(I_C)$

V_{CE} = 5 V (common emitter configuration)



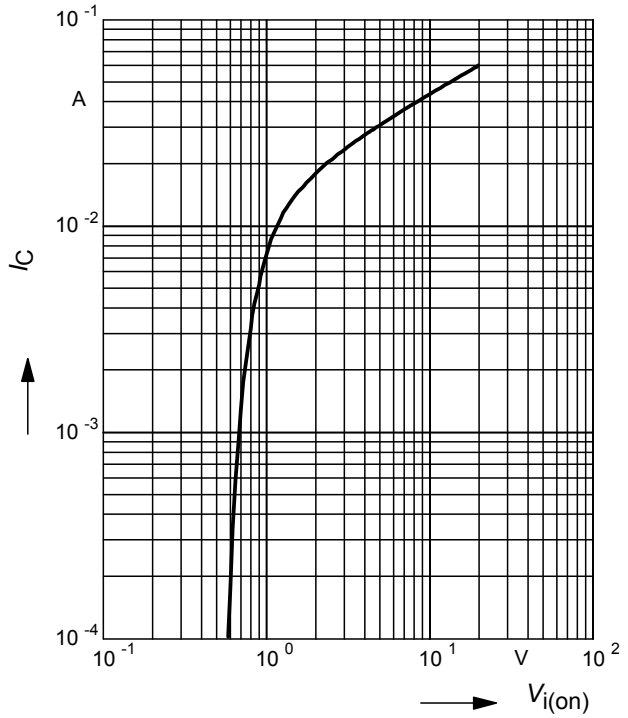
Collector-emitter saturation voltage

$V_{CEsat} = f(I_C)$, h_{FE} = 20



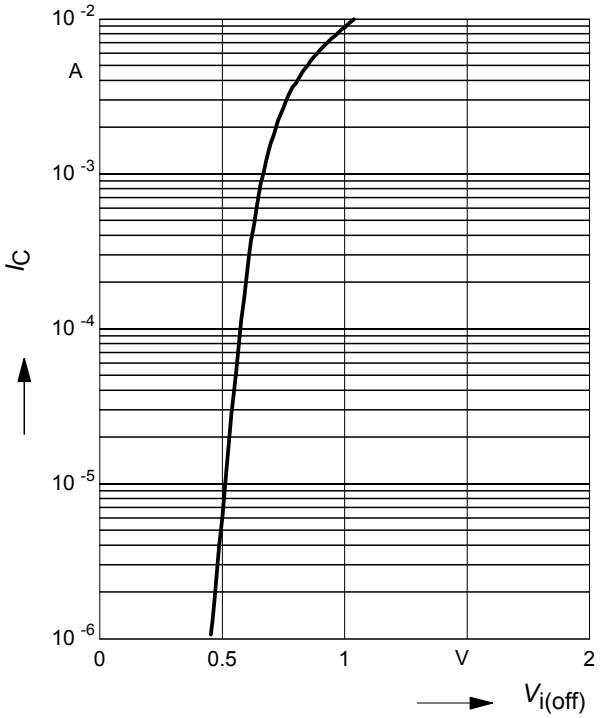
Input on Voltage $V_{i(on)} = f(I_C)$

V_{CE} = 0.3V (common emitter configuration)

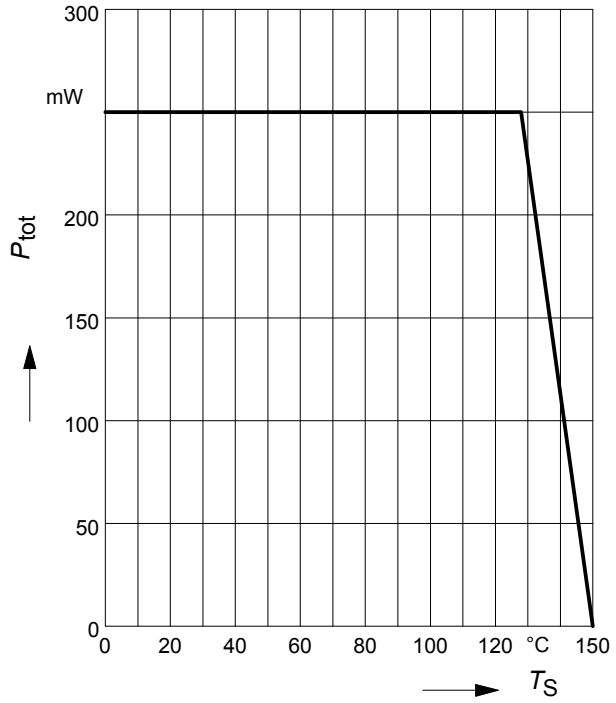


Input off voltage $V_{i(off)} = f(I_C)$

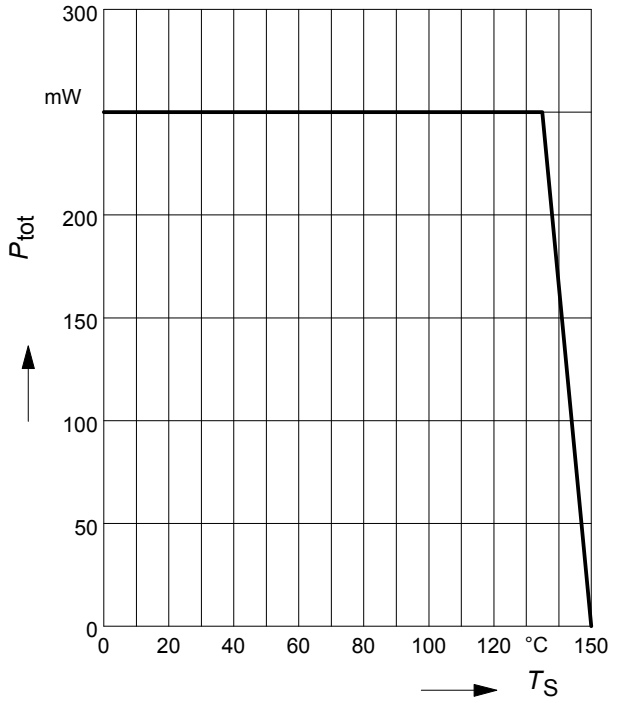
V_{CE} = 5V (common emitter configuration)



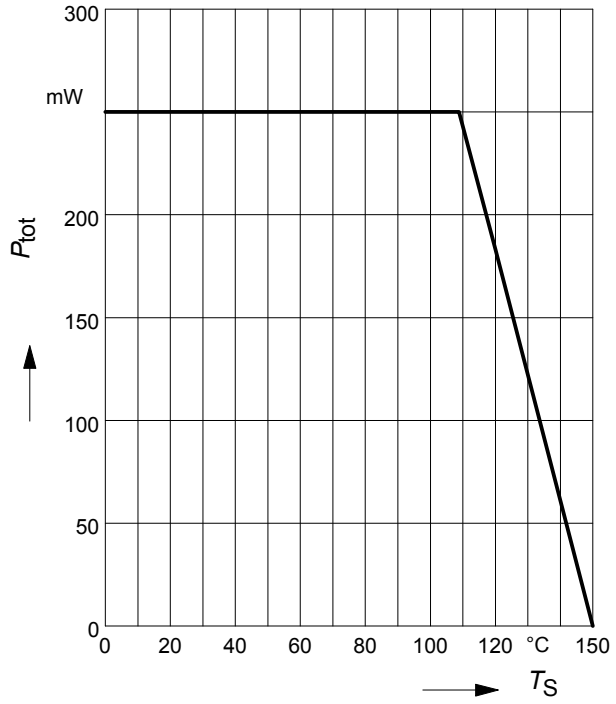
Total power dissipation $P_{tot} = f(T_S)$
BCR179F



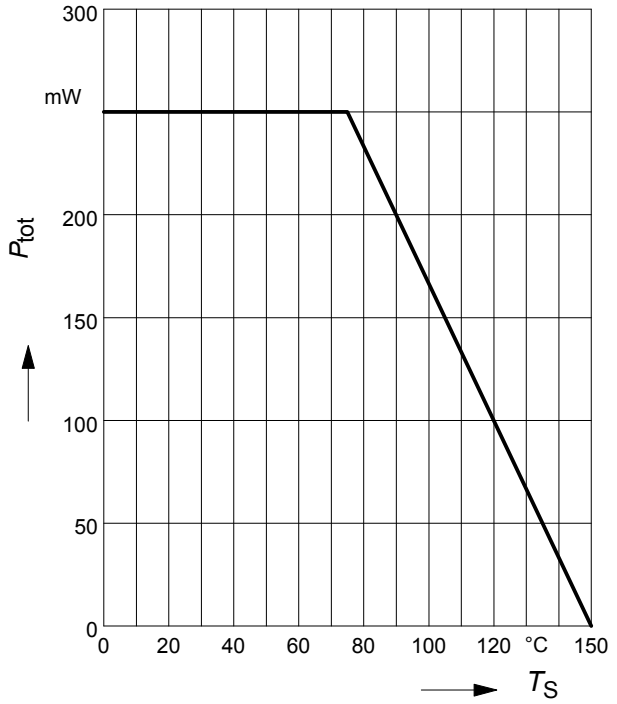
Total power dissipation $P_{tot} = f(T_S)$
BCR179L3



Total power dissipation $P_{tot} = f(T_S)$
BCR179T

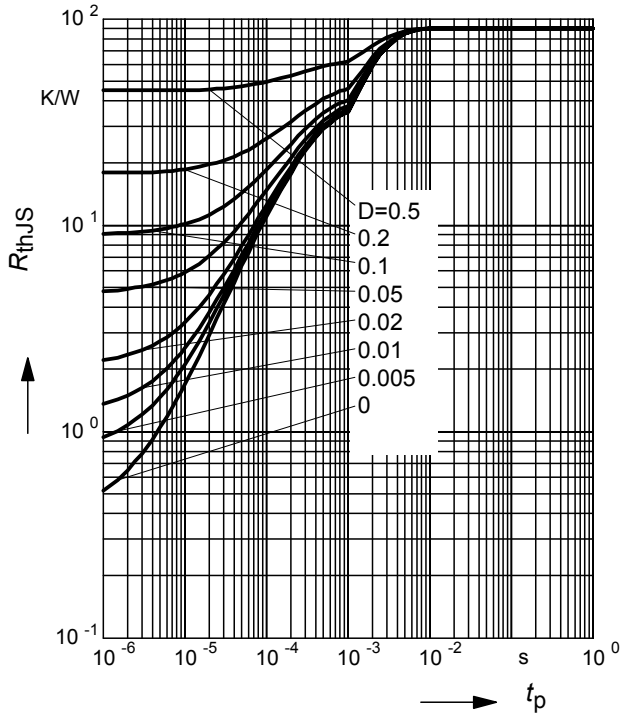


Total power dissipation $P_{tot} = f(T_S)$
SEMB4



Permissible Puls Load $R_{thJS} = f(t_p)$

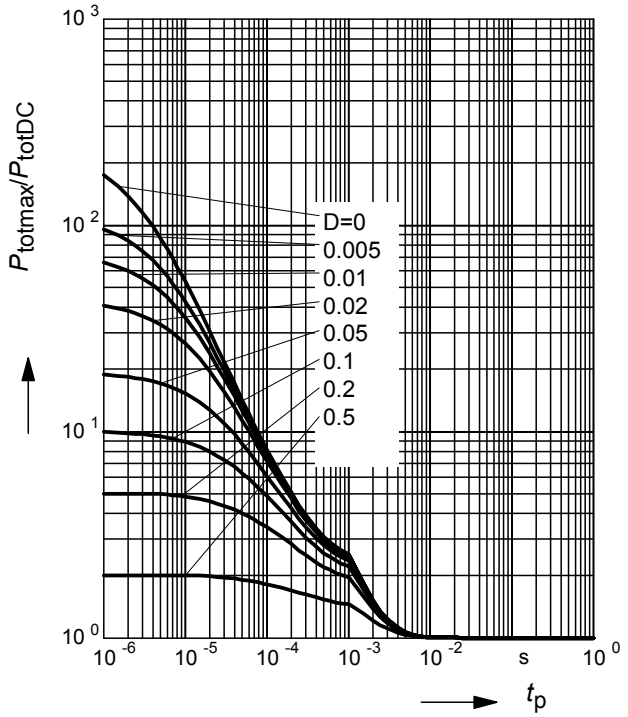
BCR179F



Permissible Pulse Load

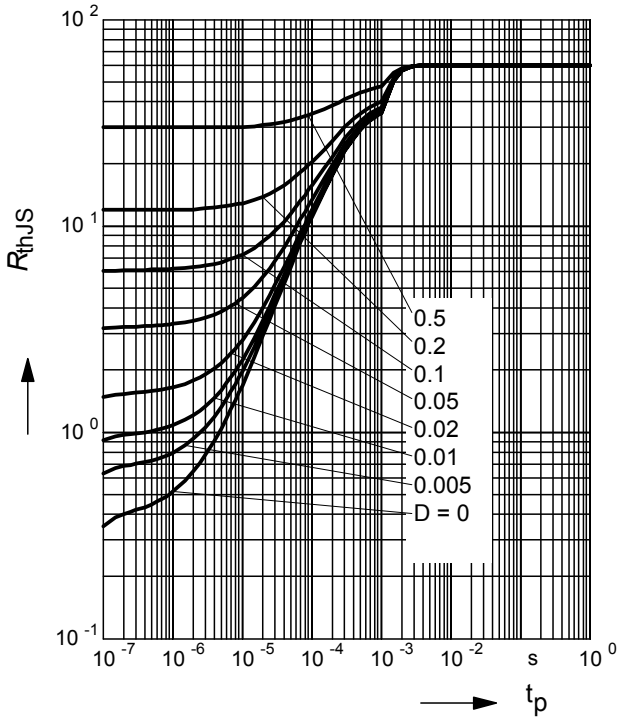
$P_{totmax}/P_{totDC} = f(t_p)$

BCR179F



Permissible Puls Load $R_{thJS} = f(t_p)$

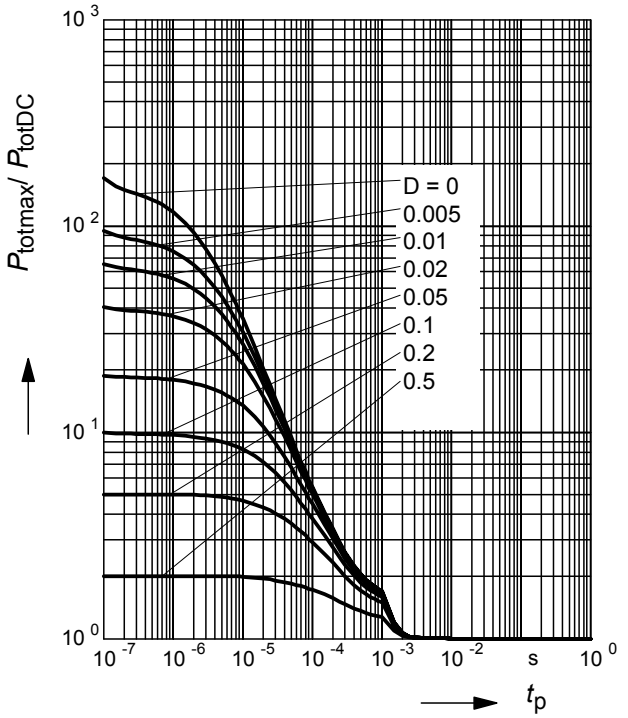
BCR179L3



Permissible Pulse Load

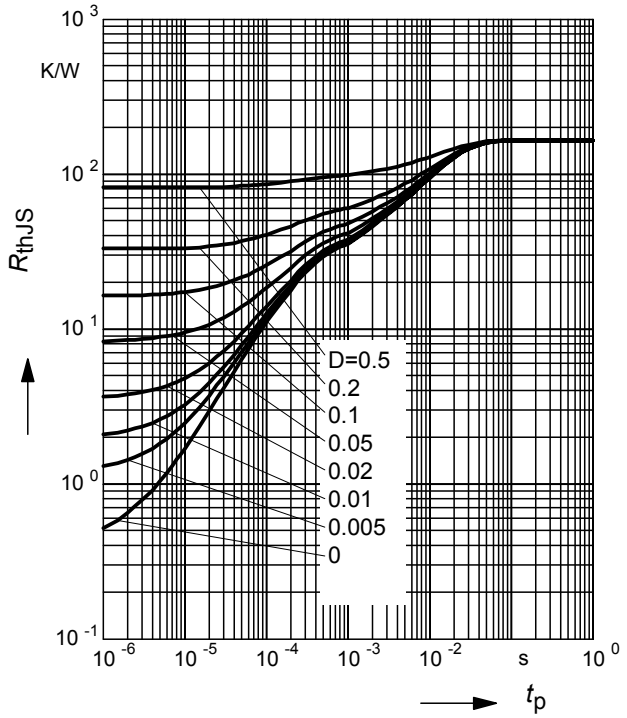
$P_{totmax}/P_{totDC} = f(t_p)$

BCR179L3



Permissible Puls Load $R_{thJS} = f(t_p)$

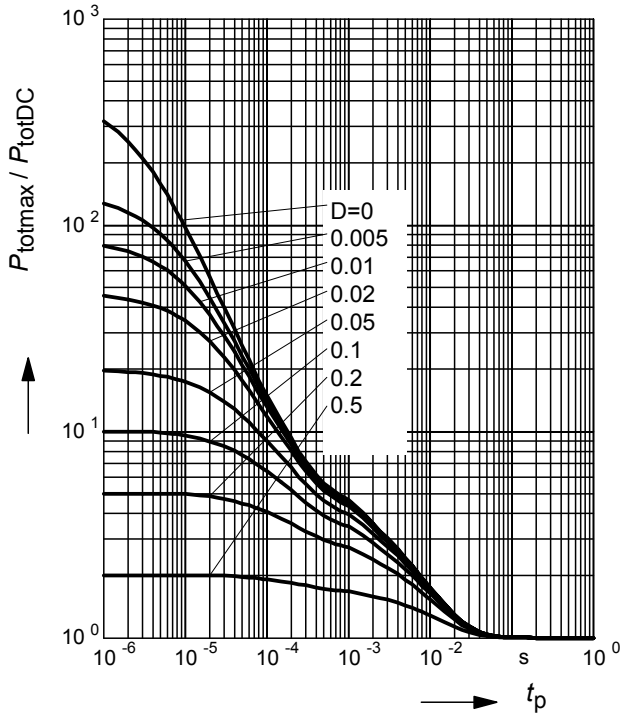
BCR179T



Permissible Pulse Load

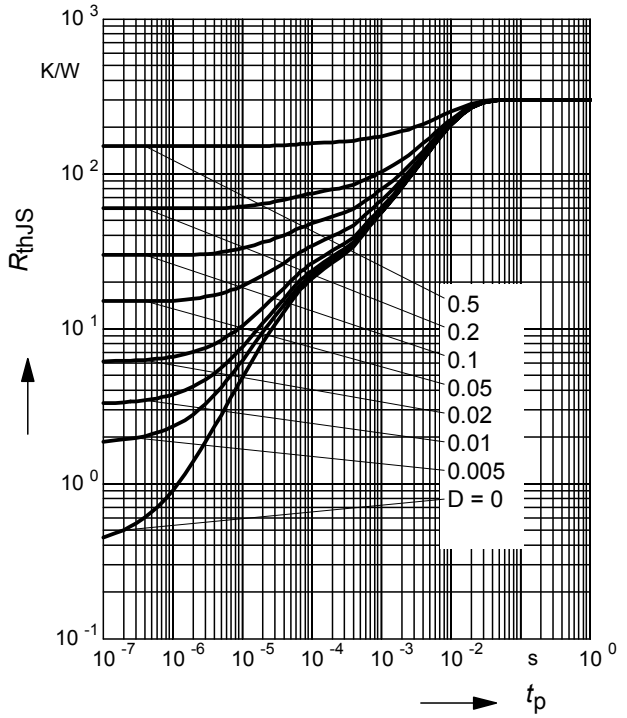
$P_{totmax}/P_{totDC} = f(t_p)$

BCR179T



Permissible Puls Load $R_{thJS} = f(t_p)$

SEMB4



Permissible Pulse Load

$P_{totmax}/P_{totDC} = f(t_p)$

SEMB4